

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Noriaki HARA et al.

Group Art Unit: Unassigned

Application No.: CIP Appln. of 09/463,967

Examiner: Unassigned

Filed: March 8, 2002

Atty. Dkt. No.: 108384-00045

For: SPUTTERING TARGET MATERIAL

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

March 8, 2002

Sir:

Prior to the examination of the above-referenced application on the merits, please amend the above-referenced application on the merits.

**IN THE SPECIFICATION:**

Please substitute the specification from U.S. Application No. 09/463,967 with the attached specification. A marked-up copy of the 09/463,967 application is included pursuant to 37 C.F.R. §1.121.

**IN THE CLAIMS:**

Please cancel claims 1-8 without prejudice or disclaimer, and add new claims 9-23 as follows:

9. (New) A platinum sputtering target material, wherein said target material containing columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (200) face to that of another arbitrary crystal face as determined

by X-ray diffractometry is greater than the corresponding ratio as measured for a powder platinum sample.

10. (New) A ruthenium sputtering target material, wherein said target material containing columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (112) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.

11. (New) A ruthenium sputtering target material, wherein said target material containing columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (002) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.

12. (New) A ruthenium sputtering target material, wherein said target material containing columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (004) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.

13. (New) An iridium sputtering target material, wherein said target material containing columnar crystals grown in a direction normal to a sputtering surface, and a ratio

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of an integral intensity of a (220) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder iridium sample.

14. (New) A sputtering target material according to claim 9, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

15. (New) A sputtering target material according to claim 10, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

16. (New) A sputtering target material according to claim 11, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

17. (New) A sputtering target material according to claim 12, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

18. (New) A sputtering target material according to claim 13, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

19. (New) A sputtering target material according to claim 14, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

20. (New) A sputtering target material according to claim 15, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

21. (New) A sputtering target material according to claim 16, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

22. (New) A sputtering target material according to claim 17, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

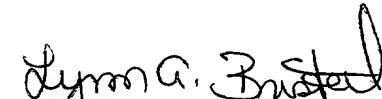
23. (New) A sputtering target material according to claim 18, wherein a crystallographic microstructure containing columnar crystals is electrodeposited from a solution containing a precious metal salt.

#### REMARKS

Claims 9-23 are all the pending claims for this C-I-P application, and the claimed subject matter finds support in the newly filed specification.

In the event this paper is not considered to be timely filed, Applicants respectfully petition for an appropriate extension of time. The Commissioner is authorized to charge payment for any additional fees which may be required with respect to this paper to Counsel's Deposit Account 01-2300.

Respectfully submitted,

  
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